

Applicant(s): Sung-bae Park, *et al.*

Serial No.: 09/924,787

B1
an isolation region adjacent to and at least partially surrounding the body; and
a body contact supplying power to the body,
wherein the body contact is formed by forming a trench that perforates the isolation
region, the body, and the buried oxide layer and filling the trench with a conductive
material so that the body is electrically connected to the semiconductor substrate.

A Sub C7
2. (Amended) The SOI MOSFET of claim 1, wherein the gate is formed of at least
one material selected from the group consisting of metal and polysilicon.

Sub D2
3. (Amended) The SOI MOSFET of claim 1, wherein the conductive material is
formed of one material selected from the group consisting of a metal layer, a tungsten layer, a
silicon epitaxial layer, and a combination layer of at least two of a metal layer, a tungsten layer
and a silicon epitaxial layer.